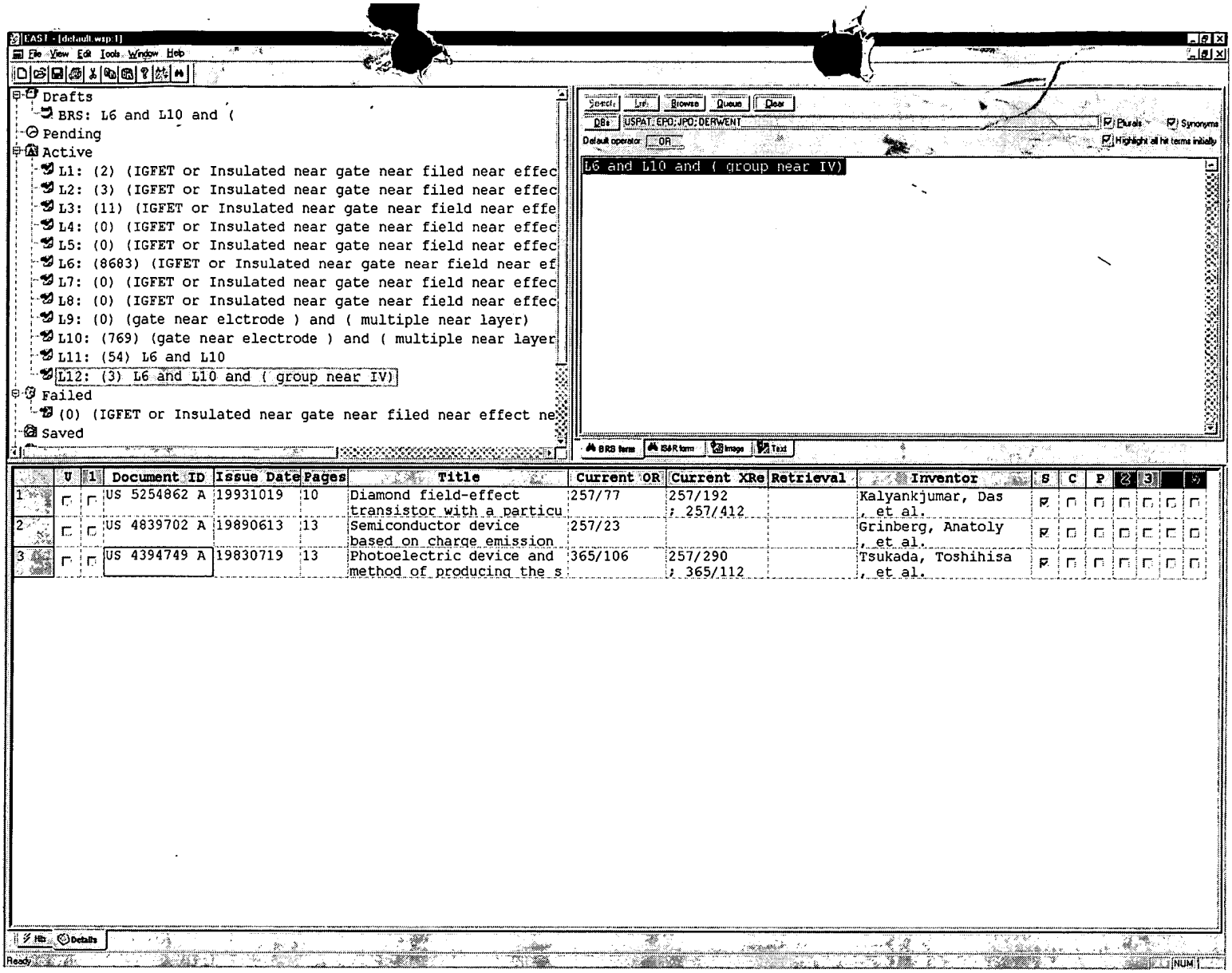
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Drafts
BRS: L6 and L10 and (
Pending
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L1: (2) (IGFET or Insulated near gate near filed near effec
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L4: (0) (IGFET or Insulated near gate near field near effec
L5: (0) (IGFET or Insulated near gate near field near effec
L6: (8683) (IGFET or Insulated near gate near field near ef
L7: (0) (IGFET or Insulated near gate near field near effec
L8: (0) (IGFET or Insulated near gate near field near effec
L9: (0) (gate near elctrode) and (multiple near layer)
L10: (769) (gate near electrode) and (multiple near layer
L11: (54) L6 and L10
L12: (3) L6 and L10 and (group near IV)
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257/192 ; 257/412
Kalyankjumar, Das , et al.
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US 4839702 A
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13
Semiconductor device based on charge emission
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Grinberg, Anatoly , et al.
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US 4394749 A
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